

ULTRA-HIGH SPEED SWITCHING APPLICATIONS
ANALOG SWITCH APPLICATIONS

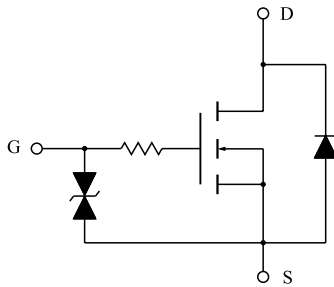
FEATURES

- 2.5 Gate Drive.
- Low Threshold Voltage : $V_{th}=0.5 \sim 1.5V$.
- High Speed.
- Small Package.
- Enhancement-Mode.

MAXIMUM RATINGS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
DC Drain Current	I_D	200	mA
Drain Power Dissipation	P_D	200	mW
Channel Temperature	T_{ch}	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

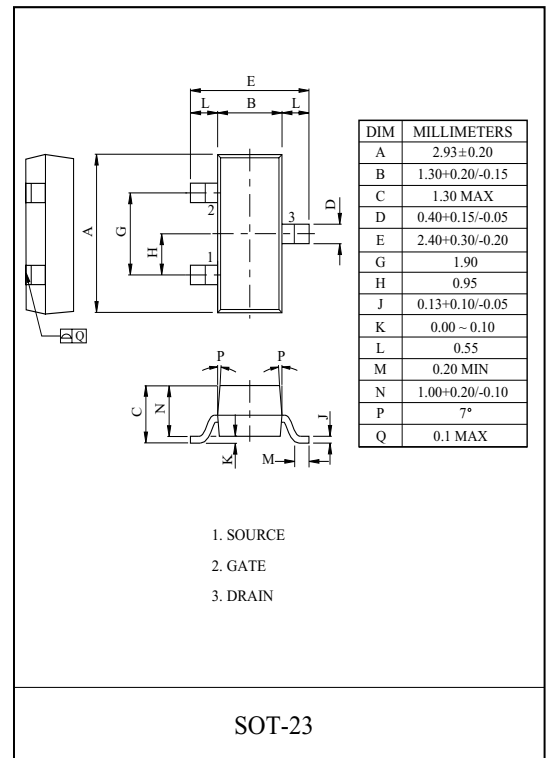
EQUIVALENT CIRCUIT



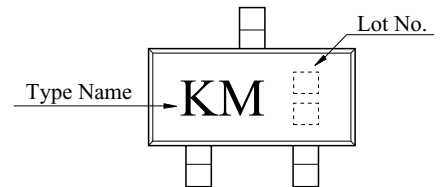
THIS TRANSISTOR IS ELECTROSTATIC SENSITIVE DEVICE.
PLEASE HANDLE WITH CAUTION.

ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT				
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	-	-	± 1	μA				
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 100 \mu A, V_{GS} = 0V$	60	-	-	V				
Drain Cut-off Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	μA				
Gate Threshold Voltage	V_{th}	$V_{DS} = 10V, I_D = 1mA$	0.5	-	1.5	V				
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 50mA$	100	-	-	mS				
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D = 50mA, V_{GS} = 2.5V$	-	1.5	2					
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$	-	55	65	pF				
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$	-	13	18	pF				
Output Capacitance	C_{oss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$	-	40	50	pF				
Switching Time	Rise Time	t_r					-	-	nS	
	Turn-on Time	t_{on}					-	8		-
	Fall Time	t_f					-	14		-
	Turn-off Time	t_{off}					-	35		-
			-	75	-					

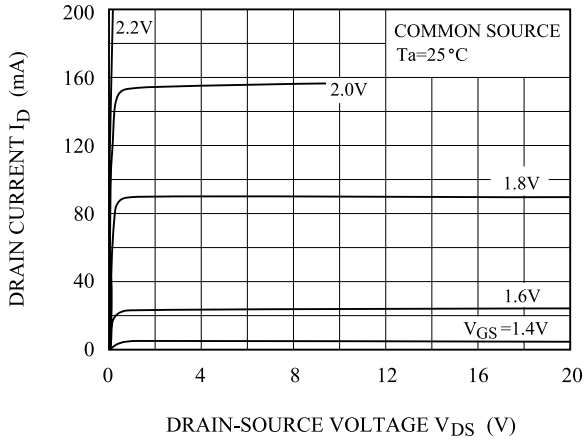


Marking

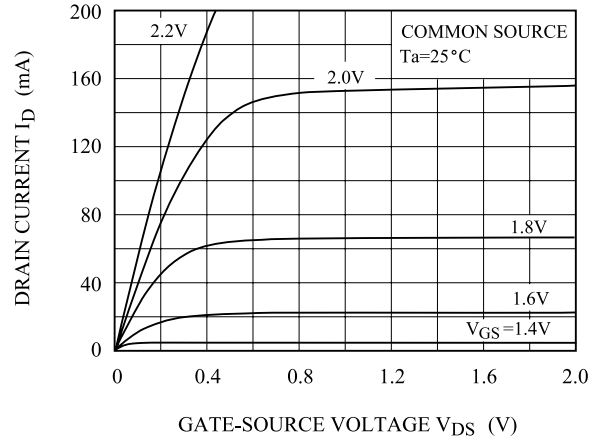


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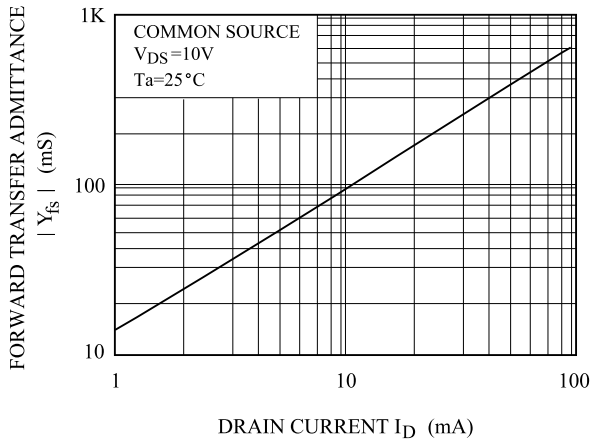
$I_D - V_{DS}$



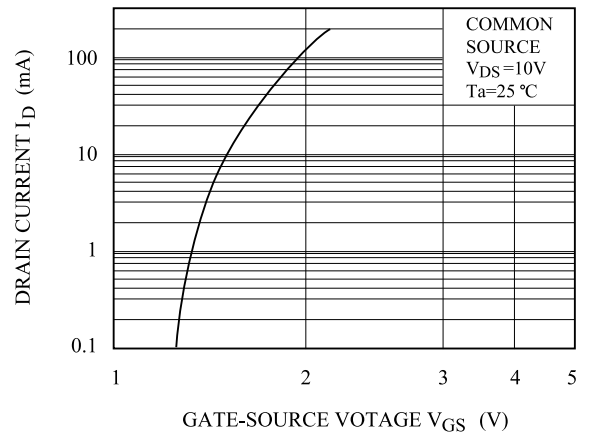
$I_D - V_{DS}$
(LOW VOLTAGE REGION)



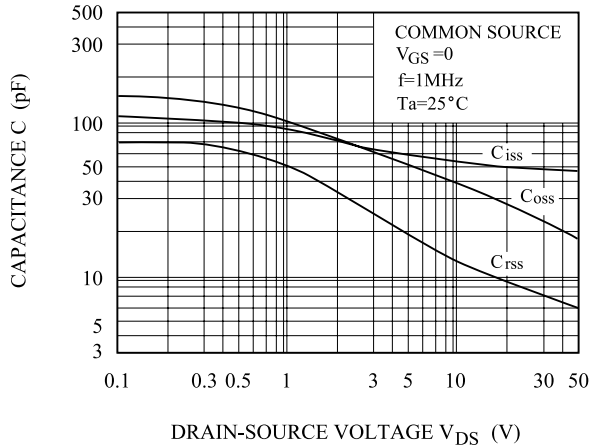
$|Y_{fs}| - I_D$



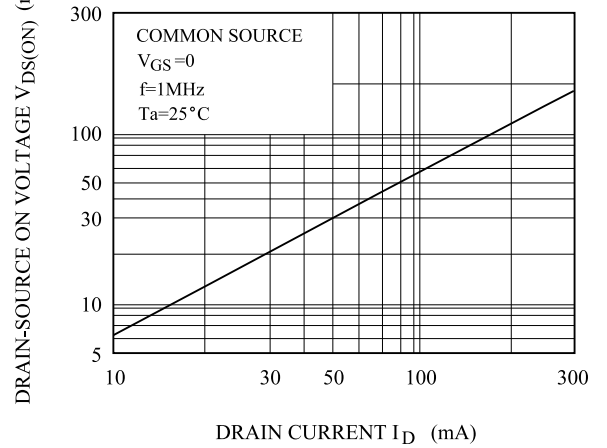
$I_D - V_{GS}$



$C - V_{DS}$

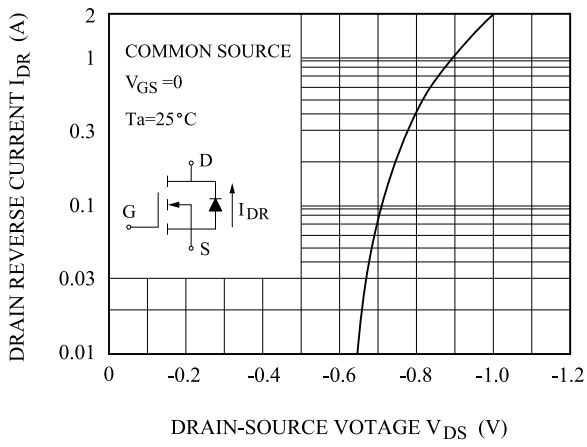


$V_{DS(ON)} - I_D$

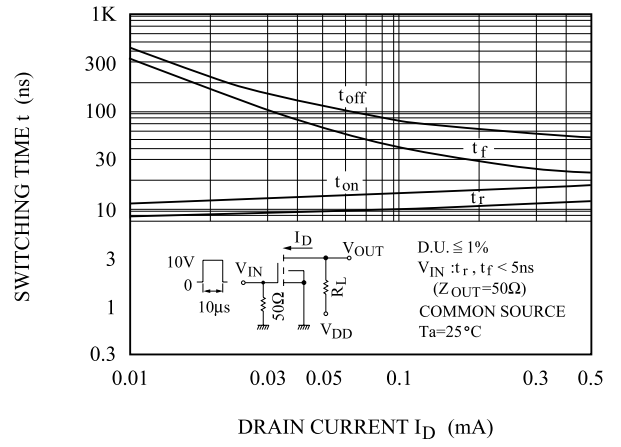


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$I_{DR} - V_{DS}$



$t - I_D$



$P_D - T_a$

